

In the Claims:

Please rewrite claims 1, 3-5, 8 and 9 as follows:

1. (Currently Amended) A semiconductor light-emitting element comprising:
a substrate,
a first epitaxial layer group to emit a yellow color light ~~which is provided on the~~
substrate and made of II-VI semiconductor compounds, and
a second epitaxial layer group to emit a blue color light ~~which is provided on the~~
substrate and made of II-VI semiconductor compounds.
- B' 2. (Original) A semiconductor light-emitting element as defined in claim 1, wherein
the first epitaxial layer group includes a light-emitting active layer made of a II-VI
semiconductor compound containing Zn, Se, Te and Cd.
3. (Currently Amended) A semiconductor light-emitting element as defined in claim 2,
wherein the light-emitting active layer is made of a II-VI semiconductor compound having a
composition of $\text{Zn}_{1-x}\text{Cd}_x\text{Se}_{1-y}\text{Te}_y$ ($0.1 < x \leq 0.4$, $0.1 < y < 0.4$).
4. (Currently Amended) A semiconductor light-emitting element as defined in claim 2;
wherein the first epitaxial layer group includes a first optical waveguide layer and a second
optical waveguide layer which ~~are provided so as to sandwich the light-emitting active layer~~
and are made of II-VI semiconductor compounds containing Be and Mg, respectively.
5. (Currently Amended) A semiconductor light-emitting element as defined in claim 4;
wherein the first epitaxial layer group includes a first cladding layer and a second cladding

| layer which ~~are provided so as to~~ sandwich the first optical waveguide layer and the second
| optical waveguide layer mon the outside of the first and the second optical waveguide layers,
| and are made of II-VI semiconductor compounds containing Be and Mg, respectively.

6. (Original) A semiconductor light-emitting element as defined in claim 1, wherein
the second epitaxial layer group includes a light-emitting active layer made of a II-VI
semiconductor compound containing Zn, Se, Te and Cd.

7. (Original) A semiconductor light-emitting element as defined in claim 6, wherein
the light-emitting active layer is made of a II-VI semiconductor compound having a
composition of $\text{Zn}_{1-Z}\text{Cd}_Z\text{Se}_{1-V}\text{Te}_V$ ($0 < Z < 0.1$, $0 < V < 0.1$).

8. (Currently Amended) A semiconductor light-emitting element as defined in claim 6,
wherein the second epitaxial layer group includes a first optical waveguide layer and a second
| optical waveguide layer which ~~are provided so as to~~ sandwich the light-emitting active layer
| and are made of II-VI semiconductor compounds containing Be and Mg, respectively.

9. (Currently Amended) A semiconductor light-emitting element as defined in claim 8,
wherein the second epitaxial layer group includes a first cladding layer and a second cladding
| layer which ~~are provided so as to~~ sandwich the first optical waveguide layer and the second
| optical waveguide layer mon the outside of the first and the second optical waveguide layers,
| and are made of II-VI semiconductor compounds containing Be and Mg, respectively.
